

## EAST Search History

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7465	(SOI GeSi1 GS1 GS1Cl GS1O1 (silicon Si) adj insulator buried adj oxide) same (ion near5 (implant\$7 bombard\$7 inject\$7 dope doping dopant oxygen "O.sub.2" "B.u/c." Ga Al BF "BF. sub.2" boron gallium aluminum))	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L2	5122	(Vacancies voids pores porosity damage\$5 dangling adj bonds) Same (anodic anodization electrolytic) same (semiconductor Si silicon germanium Ge SiGe GeSi dopant doping dose\$2)	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L3	711	(SOI GeSi1 GS1 GS1Cl GS1O1 (silicon Si) adj insulator buried adj oxide) same (ion near5 (implant\$7 bombard\$7 inject\$7) with ((S silicon) near ion "Si.sup.+" Ge germanium Ne neon Bi bismuth Sn "tin./c.))	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L4	29	L2 and L1 and L3	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L5	11681	((427/526,527,529,539,579,533) or (438/798,766,770,771,772,787,788,453,440,439,423,407,378,297) or (205/123,157,316)). Cols.	US_PGPUB; USPAT; USOCH; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/17 14:50
L6	7465	(SOI GeSi1 GS1 GS1Cl GS1O1 (silicon Si) adj insulator buried adj oxide) same (ion near5 (implant\$7 bombard\$7 inject\$7 dope doping dopant oxygen "O.sub.2" "B.u/c." Ga Al BF "BF. sub.2" boron gallium aluminum))	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L7	5122	(Vacancies voids pores porosity damage\$5 dangling adj bonds) Same (anodic anodization electrolytic) same (semiconductor Si silicon germanium Ge SiGe GeSi dopant doping dose\$2)	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50

L8	71	L6 same L7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L9	257	L6 and L7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L10	71	L8 and L9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L11	186	L9 not L10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L12	2358	("HF.u.c." Hydrofluoric hydrofluoride Hydrofloric hydrofluoride Hydrofluoricacid hydrofluorideacid Hydro adj (fluoride fluoric floric)) Same (anodic anodization electrolytic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L13	57	L11 and L12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L14	1	L13 and L5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L15	56	L13 not L14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50

L16	129	L11 not (L10 or L14 or L15)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L17	31	L10 and L12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L18	129	L11 not (L10 or L14 or L15)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L19	57	L18 and (Vacancies voids pores porous porosity ) with (percent percentages "%" grade\$2 grading different differential\$3 differential\$4 vary\$4 varied)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L20	257	L10 or L14 or L15 or L16 or L17 or L19 or L4	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:50
L21	3	L20 and @pd>"20090912"	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/17 14:53

## EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L22	82	((427/526,527,529,539,579,533) or ((438/798,766,770,771,772,787,788,453,440,439,423,407,378,297) or (205/123,157,316)).COLS.	UPAD	OR	OFF	2009/12/17 14:56
L23	152	(SOI GeSOI GSOI GeSiO1 (silicon Si) adj insulator buried adj oxide) same (ion near5 (implant \$7 bombard\$7 inject\$7 dope doping dopant oxygen "O.sub.2" "B.u/c." Ga Al BF "BF.sub.2" boron gallium aluminum))	UPAD	OR	ON	2009/12/17 14:56
L24	57	(Vacancies voids pores porous porosity damage\$5 dangling adj bonds) same (anodic anodization electrolytic) same (semiconductor Si silicon germanium Ge SGe GeSi dopant doping dose\$2)	UPAD	OR	ON	2009/12/17 14:56

L25	0	L23 same L24	UPAD	OR	ON	2009/12/17 14:56
L26	1	L23 and L24	UPAD	OR	ON	2009/12/17 14:56
L27	15	("HF.u/c." Hydrofluoric hydrofluoride Hydrofloric hydrofluoride Hydrofluoricacid hydrofluorideacid [Hydro adj (fluoride fluoric floric) Same (anodic anodization electrolytic)	UPAD	OR	ON	2009/12/17 14:56
L28	0	L26 and L27	UPAD	OR	ON	2009/12/17 14:56
L29	0	L26 and L22	UPAD	OR	ON	2009/12/17 14:56
L30	1	L26 and (Vacancies voids pores porous porosity ) with (percent percentages "%" grade\$2 grading different differential\$3 differential\$4 vary\$4 varied)	UPAD	OR	ON	2009/12/17 14:56
L31	4	L22 and (L23 or L24)	UPAD	OR	ON	2009/12/17 14:56
L32	1	L26 or L30	UPAD	OR	ON	2009/12/17 14:56
L33	5	L25 or L26 or L28 or L29 or L30 or L31 or L32	UPAD	OR	ON	2009/12/17 14:58

12/17/2009 3:04:12 PM

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